

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

# RN1910FE,RN1911FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN2910FE, RN2911FE

#### **Equivalent Circuit and Bias Resistor Values**



### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ι <sub>C</sub>	100	mA
Collector power dissipation	P <sub>C</sub> (Note)	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating



Weight: g (typ.)

## Equivalent Circuit (top view)



Unit: mm

### Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	$V_{CB}=50~V,~I_{E}=0$			100	nA
Emitter cut-off current		I <sub>EBO</sub>	$V_{EB} = 5 V, I_{C} = 0$			100	nA
DC current gain		h <sub>FE</sub>	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	120	_	700	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	$I_{C} = 5 \text{ mA}, I_{B} = 0.25 \text{ mA}$		0.1	0.3	V
Transition frequency		f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$		250	_	MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3	6	pF
Input resistor	RN1910FE	- R1	_	3.29	4.7	6.11	kΩ
	RN1911FE			7	10	13	



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